

Very low capacitance bidirectional ESD protection diodeRev. 1 — 3 April 2012Product data

Product data sheet

1. **Product profile**

1.1 General description

Very low capacitance bidirectional ElectroStatic Discharge (ESD) protection diode designed to protect one signal line from the damage caused by ESD and other transients. The device is housed in a leadless ultra small DFN1006-2 (SOD882) Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- Bidirectional ESD protection of one line ESD protection up to 30 kV
- Low diode capacitance $C_d = 17 \text{ pF}$
- Rated peak pulse power: P_{PPM} = 290 W IEC 61000-4-5 (surge); I_{PPM} = 7.8 A
- Ultra low leakage current I_{RM} < 1 nA</p>

1.3 Applications

- Computers and peripherals
- Audio and video equipment
- Cellular handsets and accessories

1.4 Quick reference data

Quick reference data Table 1.

 $T_{amb} = 25 \ ^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RWM}	reverse standoff voltage		-	-	12	V
C _d	diode capacitance	$f = 1 \text{ MHz}; V_R = 0 \text{ V}$	-	17	25	pF

Pinning information 2.

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	cathode		
2	cathode	1 2	1 2 sym045
		Transparent top view	



- IEC 61000-4-2; level 4 (ESD)
- AEC-Q101 qualified
- Portable electronics
- Communication systems

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3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PESD12VV1BL	DFN1006-2	leadless ultra small plastic package; 2 terminals; body $1.0 \times 0.6 \times 0.5$ mm	SOD882			

4. Marking

Table 4. Marking codes	
Type number	Marking code
PESD12VV1BL	MW

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

P_{PPM} rated peak pulse power[1] -290W I_{PPM} rated peak pulse current $t_p = 8/20 \ \mu s$ [1] -7.8A T_j junction temperature-150°C	Symbol	Parameter	Conditions	Min	Max	Unit
	P _{PPM}	rated peak pulse power		<u>[1]</u> _	290	W
T_j junction temperature - 150 °C	I _{PPM}	rated peak pulse current	t _p = 8/20 μs	<u>[1]</u> _	7.8	А
	T _j	junction temperature		-	150	°C
T _{amb} ambient temperature -55 +150 °C	T _{amb}	ambient temperature		-55	+150	°C
T_{stg} storage temperature -65 +150 °C	T _{stg}	storage temperature		-65	+150	°C

[1] Device stressed with ten non-repetitive current pulses (8/20 μs exponential decay waveform according to IEC 61000-4-5 and IEC 61643-321).

Table 6. ESD maximum ratings

 $T_{amb} = 25$ °C unless otherwise specified.

• • •	_	A 11/1			
Symbol	Parameter	Conditions	Min	Max	Unit
V _{ESD}	electrostatic discharge voltage	IEC 61000-4-2 (contact discharge)	<u>[1]</u> _	30	kV
		machine model	-	400	V
		MIL-STD-883 (human body model)	-	10	kV

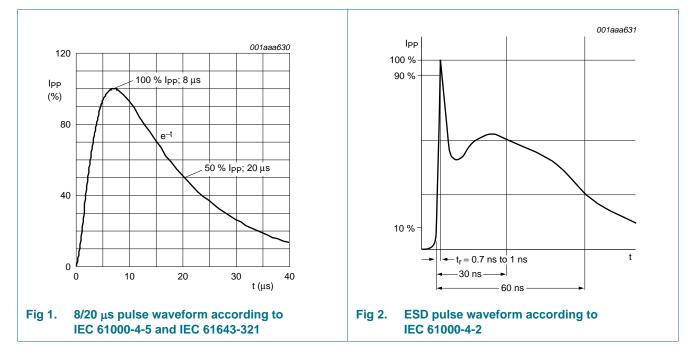
[1] Device stressed with ten non-repetitive ESD pulses.

Table 7. ESD standards compliance

Standard	Conditions
IEC 61000-4-2; level 4 (ESD)	> 15 kV (air); > 8 kV (contact)
MIL-STD-883; class 3B (human body model)	> 8 kV

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6. Characteristics

Table 8.Characteristics

 $T_{amb} = 25 \ ^{\circ}C$ unless otherwise specified.

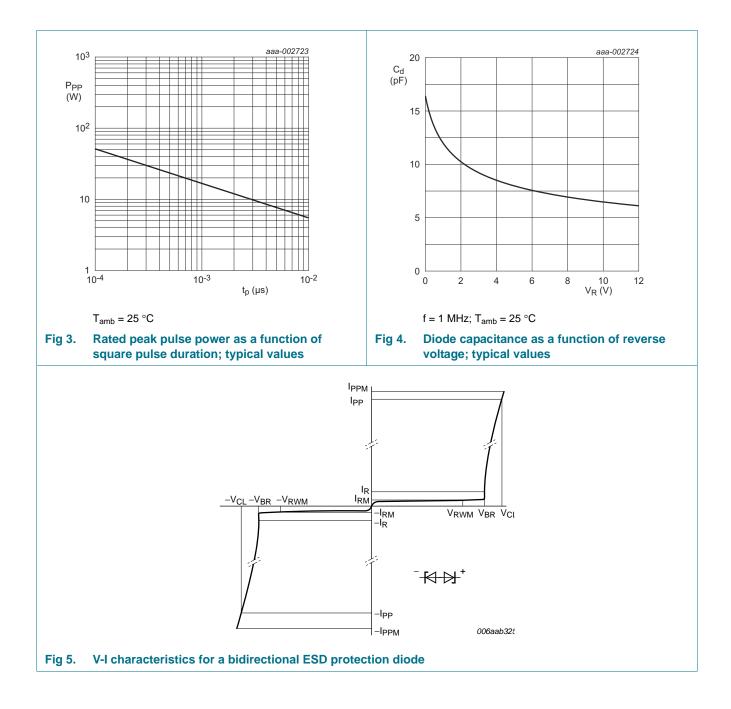
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RWM}	reverse standoff voltage			-	-	12	V
I _{RM}	reverse leakage current	$V_{RWM} = 12 V$		-	< 1	10	nA
V _{BR}	breakdown voltage	I _R = 5 mA		14.6	15.7	16.8	V
C _d	diode capacitance	$f = 1 MHz; V_R = 0 V$		-	17	25	pF
V _{CL}	clamping voltage	I _{PP} = 1 A	<u>[1]</u>	-	-	22	V
		I _{PPM} = 7.8 A	<u>[1]</u>	-	-	38	V
r _{dyn}	dynamic resistance	I _R = 10 A	[2]	-	0.7	-	Ω

[1] Device stressed with 8/20 µs exponential decay waveform according to IEC 61000-4-5 and IEC 61643-321.

[2] Non-repetitive current pulse, Transmission Line Pulse (TLP) t_p = 100 ns; square pulse; ANS/IESD STM5-1-2008.

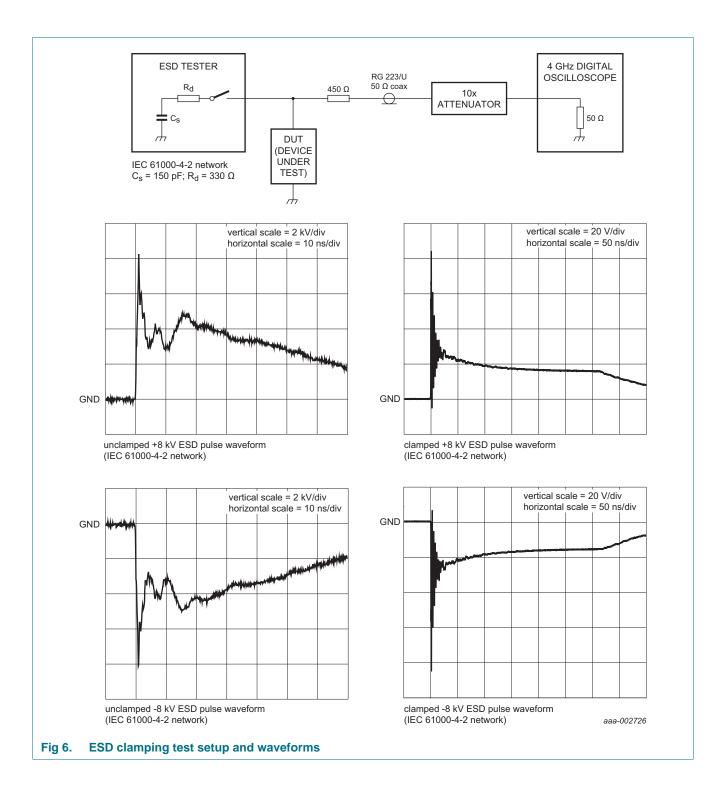
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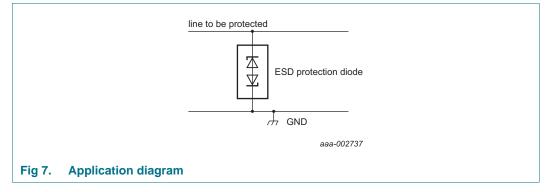


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7. Application information

The device is designed for the protection of one bidirectional data or signal line from surge pulses and ESD damage. The device is suitable on lines where the signal polarities are both, positive and negative with respect to ground.



Circuit board layout and protection device placement

Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the device as close to the input terminal or connector as possible.
- 2. Minimize the path length between the device and the protected line.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protected conductors in parallel with unprotected conductors.
- 5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Use ground planes whenever possible. For multilayer PCBs, use ground vias.

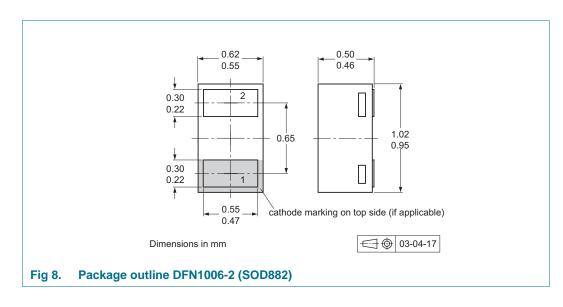
8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline



10. Packing information

Table 9. Packing methods

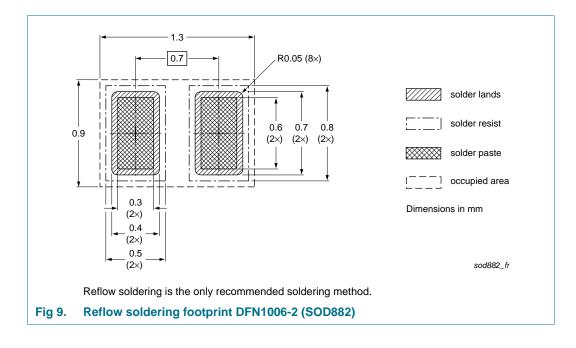
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			10000
PESD12VV1BL	DFN1006-2 (SOD882)	4 mm pitch, 8 mm tape and reel	-315

[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



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12. Revision history

Table 10. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PESD12VV1BL v.1	20120403	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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